# **Dual 2-input NAND gate**

Rev. 12 — 8 April 2013

**Product data sheet** 

### 1. General description

The 74LVC2G00 provides a 2-input NAND gate function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- $\pm$  24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



# 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G00DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G00GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74LVC2G00GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74LVC2G00GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 $\times$ 2 $\times$ 0.5 mm	SOT996-2
74LVC2G00GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 $\times$ 1.6 $\times$ 0.5 mm	SOT902-2
74LVC2G00GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 $\times$ 1.0 $\times$ 0.35 mm	SOT1116
74LVC2G00GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

# 4. Marking

Table 2. Marking codes

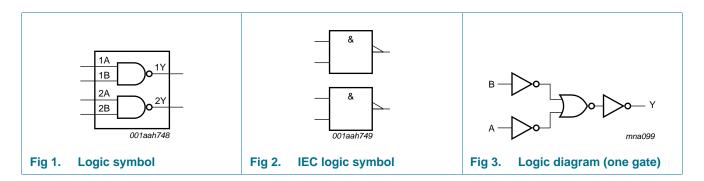
Type number	Marking code <sup>[1]</sup>
74LVC2G00DP	V2G00
74LVC2G00DC	V00
74LVC2G00GT	V00
74LVC2G00GF	VA
74LVC2G00GD	V00
74LVC2G00GM	V00
74LVC2G00GN	VA
74LVC2G00GS	VA

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

NXP Semiconductors 74LVC2G00

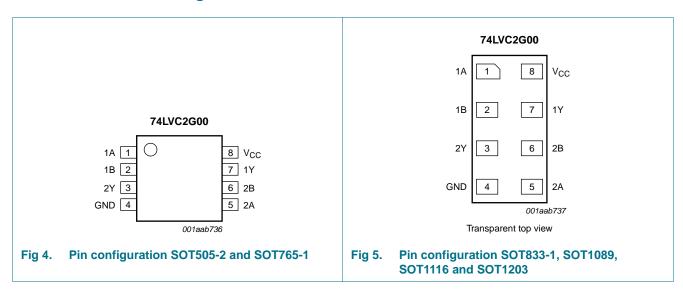
**Dual 2-input NAND gate** 

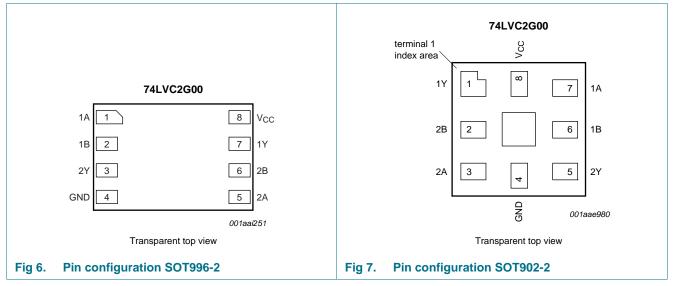
# 5. Functional diagram



### 6. Pinning information

# 6.1 Pinning





74LVC2G00

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### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin								
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2								
1A, 2A	1, 5	7, 3	data input							
1B, 2B	2, 6	6, 2	data input							
GND	4	4	ground (0 V)							
1Y, 2Y	7, 3	1, 5	data output							
V <sub>CC</sub>	8	8	supply voltage							

## 7. Functional description

Table 4. Function table [1]

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	•	mA
I <sub>OK</sub>	output clamping current	$V_O < 0 V \text{ or } V_O > V_{CC}$	-	±50	mA
I <sub>O</sub>	output current	$V_O = 0 V to V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$	<u>[3]</u> _	300	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

74LVC2G00

<sup>[2]</sup> When  $V_{CC} = 0 \text{ V}$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

<sup>[3]</sup> For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

# 9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	10	ns/V

### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +85 °C[1]					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	8.0	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -100 \mu A$ ; $V_{CC} = 1.65 V$ to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	1.53	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	2.13	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	2.50	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	2.60	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	4.10	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.08	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.14	0.3	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	0.19	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.37	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	V
l <sub>l</sub>	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ

**Dual 2-input NAND gate** 

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	0.1	10	μΑ
Δl <sub>CC</sub>	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	pF
T <sub>amb</sub> = -	40 °C to +125 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -100 \mu A$ ; $V_{CC} = 1.65 V to 5.5 V$	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
l	input leakage current	$V_I$ = 5.5 V or GND; $V_{CC}$ = 0 V to 5.5 V	-	-	±20	μΑ
l <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	40	μΑ
Δl <sub>CC</sub>	additional supply current	per pin; $V_1 = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	-	5000	μΑ

<sup>[1]</sup> All typical values are measured at  $T_{amb}$  = 25 °C.

# 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		-40	°C to +85	°C	-40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
$t_{pd}$	propagation delay	nA, nB to nY; see Figure 8	[2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	3.5	8.6	1.2	10.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	2.3	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 \text{ V}$		0.7	3.0	5.6	0.7	7.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	2.2	4.3	0.7	5.4	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.8	3.3	0.5	4.2	ns
$C_{PD}$	power dissipation capacitance	per gate; $V_I = GND$ to $V_{CC}$	[3]	-	14	-	-	-	pF

<sup>[1]</sup> Typical values are measured at nominal  $V_{CC}$  and at  $T_{amb}$  = 25 °C.

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

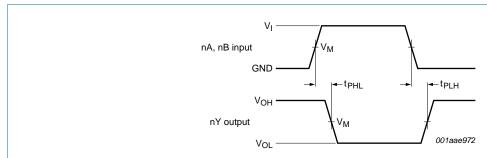
C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of outputs.

#### 12. Waveforms



Measurement points are given in Table 9.

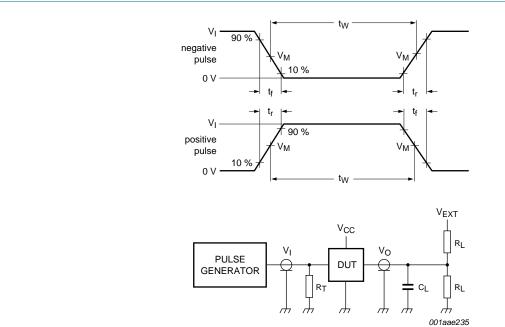
 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical output voltage levels that occur with the output load.

Fig 8. Input (nA, nB) to output (nY) propagation delays

<sup>[2]</sup> t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>

Table 9. Measurement points

Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>



Test data is given in Table 10.

Definitions for test circuit:

 $R_L$  = Load resistor.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $V_{EXT}$  = Test voltage for switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load	Load				
V <sub>CC</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>			
1.65 V to 1.95 V	V <sub>CC</sub>	$\leq$ 2.0 ns	30 pF	1 kΩ	open			
2.3 V to 2.7 V	$V_{CC}$	$\leq$ 2.0 ns	30 pF	500 Ω	open			
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open			
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open			
4.5 V to 5.5 V	V <sub>CC</sub>	≤ 2.5 ns	50 pF	500 Ω	open			

## 13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

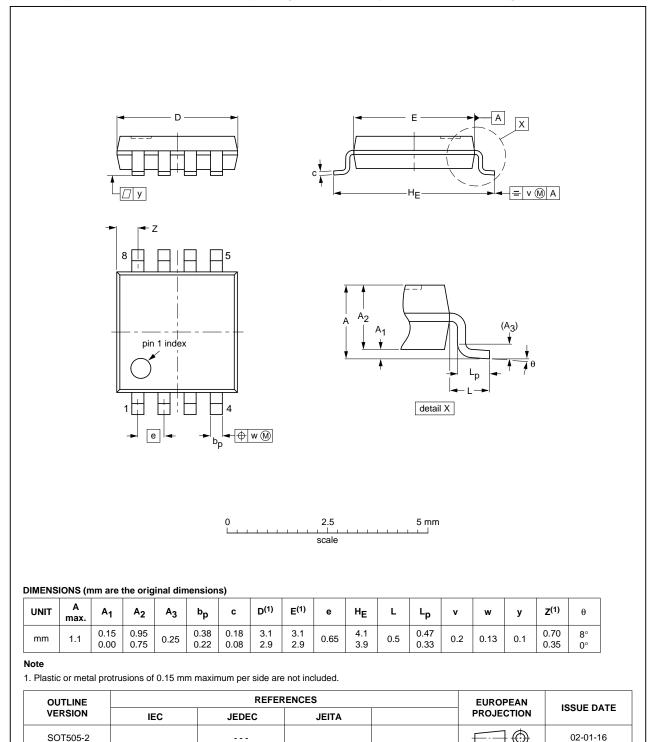
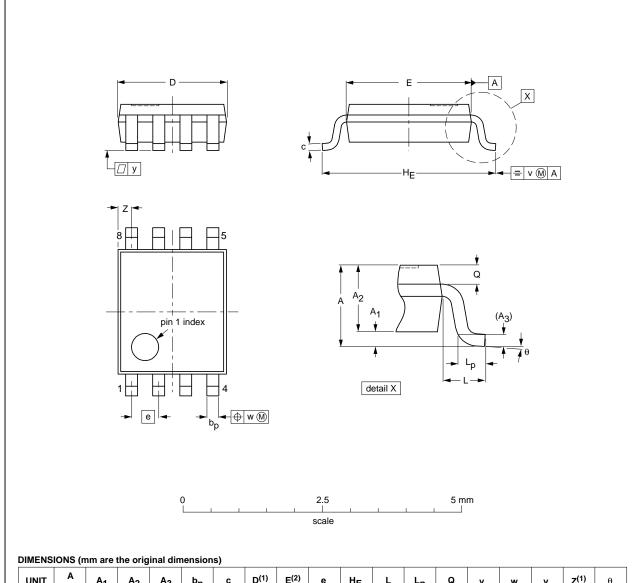


Fig 10. Package outline SOT505-2 (TSSOP8)

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#### VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	q	٧	w	у	Z <sup>(1)</sup>	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

#### Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 11. Package outline SOT765-1 (VSSOP8)

74LVC2G00

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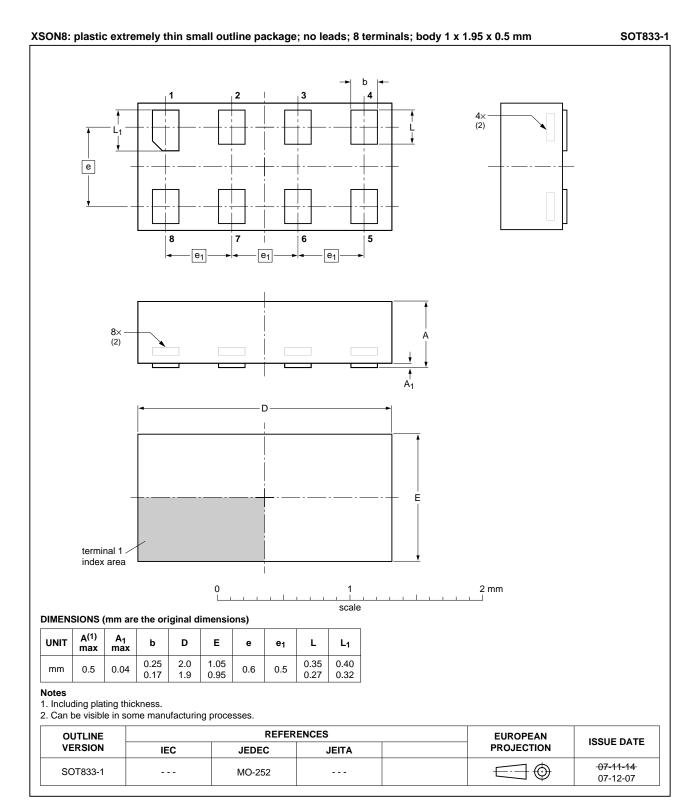


Fig 12. Package outline SOT833-1 (XSON8)

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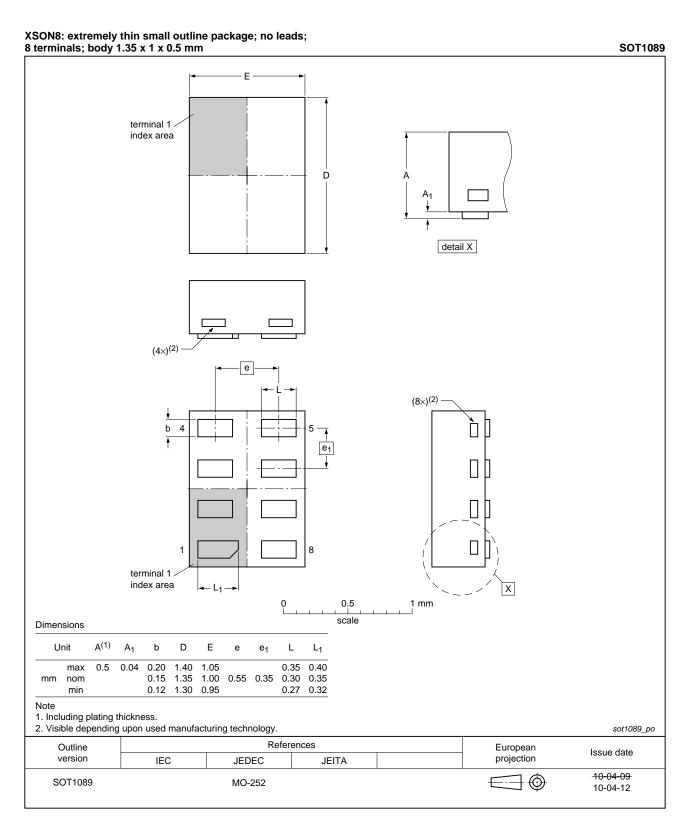


Fig 13. Package outline SOT1089 (XSON8)

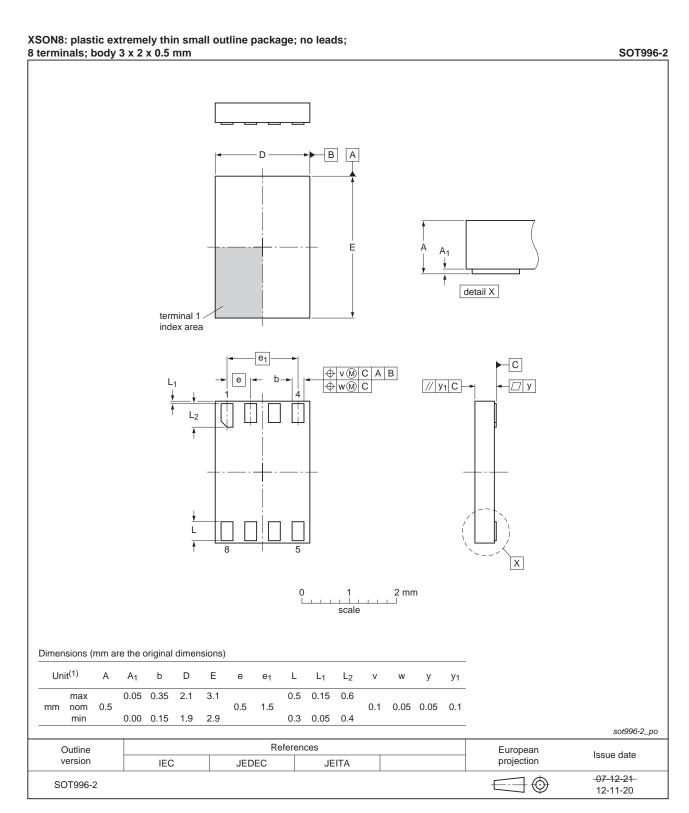


Fig 14. Package outline SOT996-2 (XSON8)

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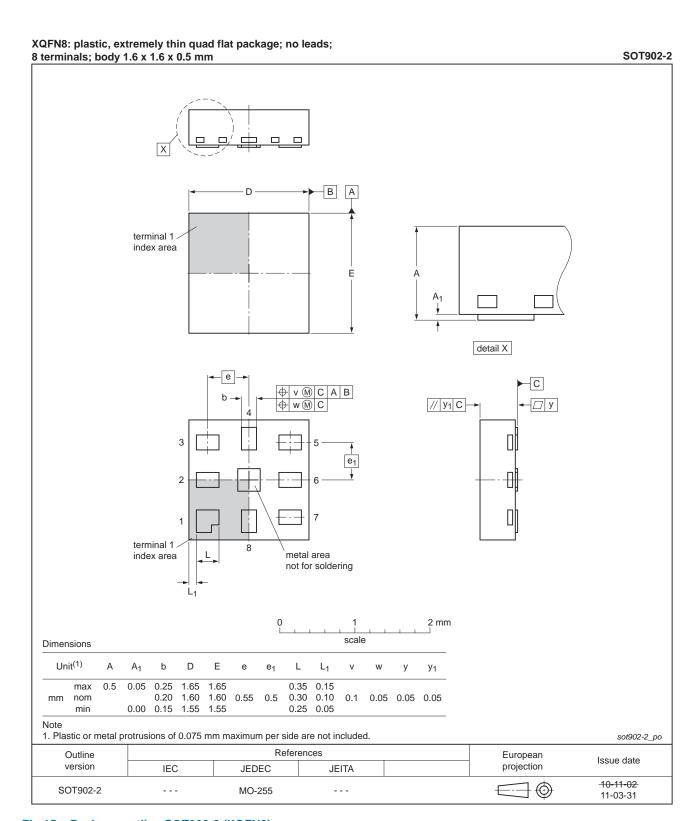


Fig 15. Package outline SOT902-2 (XQFN8)

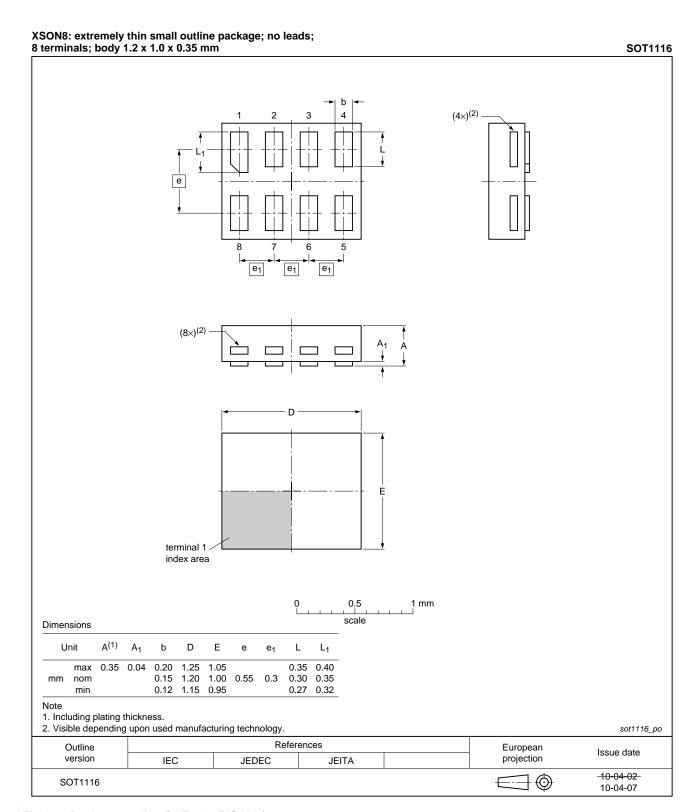


Fig 16. Package outline SOT1116 (XSON8)

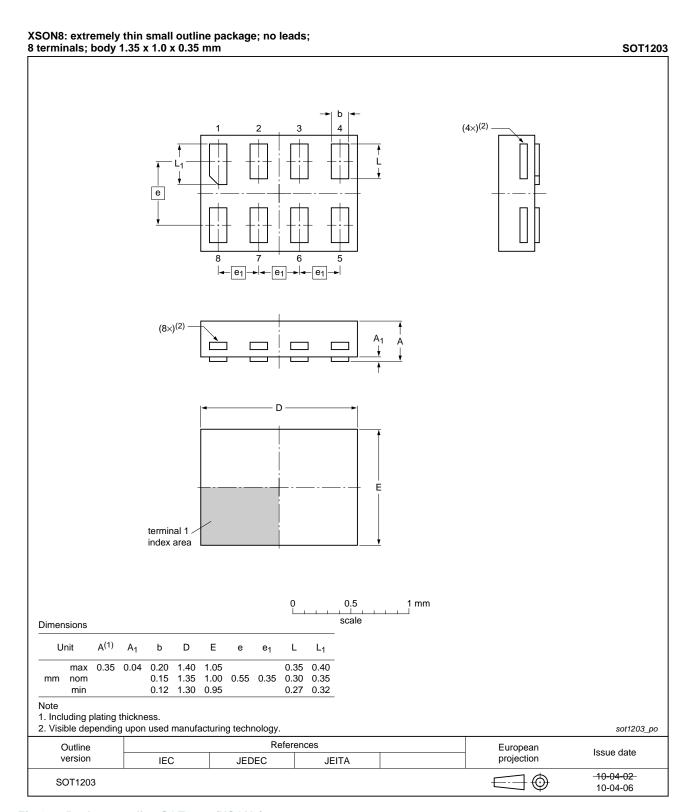


Fig 17. Package outline SOT1203 (XSON8)

## 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 15. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G00 v.12	20130408	Product data sheet	-	74LVC2G00 v.11
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G00GD XSO	N8U has changed to XS	SON8.
74LVC2G00 v.11	20120622	Product data sheet	-	74LVC2G00 v.10
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G00GM the S	OT code has changed	to SOT902-2.
74LVC2G00 v.10	20111130	Product data sheet	-	74LVC2G00 v.9
Modifications:	<ul> <li>Legal page:</li> </ul>	s updated.		
74LVC2G00 v.9	20100608	Product data sheet	-	74LVC2G00 v.8
74LVC2G00 v.8	20091026	Product data sheet	-	74LVC2G00 v.7
74LVC2G00 v.7	20080610	Product data sheet	-	74LVC2G00 v.6
74LVC2G00 v.6	20080220	Product data sheet	-	74LVC2G00 v.5
74LVC2G00 v.5	20070904	Product data sheet	-	74LVC2G00 v.4
74LVC2G00 v.4	20060515	Product data sheet	-	74LVC2G00 v.3
74LVC2G00 v.3	20050201	Product specification	-	74LVC2G00 v.2
74LVC2G00 v.2	20040923	Product specification	-	74LVC2G00 v.1
74LVC2G00 v.1	20031117	Product specification	-	-

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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#### **Dual 2-input NAND gate**

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### **Dual 2-input NAND gate**

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